List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Azimuthal angle dependent dielectric function of SnS by ellipsometry. Journal of the Korean Physical Society, 2022, 80, 59-62.	0.7	0

Role of the A-Site Cation in Low-Temperature Optical Behaviors of APbBr₃ (A = Cs,) Tj ETQq0 0 0 rgBT $_{13.7}^{10}$ Overlock $_{13}^{10}$ Tf 50 70 rgBT $_{13.7}^{10}$ Tf 50 70 rg

3	Modeling the temperature dependence of the optical properties of anisotropic SnS0.52Se0.48. Journal of the Korean Physical Society, 2021, 78, 269-274.	0.7	0
4	A Systematic Study of Compositionally Dependent Dielectric Tensors of SnSxSe1-x Alloys by Spectroscopic Ellipsometry. Crystals, 2021, 11, 548.	2.2	3
5	Maximum-entropy revisited: Optimal filtering of spectra. Journal of Applied Physics, 2021, 129, .	2.5	8
6	On the Origin of Room-Temperature Amplified Spontaneous Emission in CsPbBr ₃ Single Crystals. Chemistry of Materials, 2021, 33, 7185-7193.	6.7	9
7	Approximated dielectric tensor of the biaxial α-SnSe crystal. Journal of the Korean Physical Society, 2021, 78, 297-301.	0.7	1
8	Static Rashba Effect by Surface Reconstruction and Photon Recycling in the Dynamic Indirect Gap of APbBr ₃ (A = Cs, CH ₃ NH ₃) Single Crystals. Journal of the American Chemical Society, 2020, 142, 21059-21067.	13.7	33
9	Modeling of the Temperature Dependence of the Dielectric Function of Biaxial α-SnS. Journal of the Korean Physical Society, 2020, 77, 987-990.	0.7	0
10	Optical Properties of Anisotropic SnSxSe1â^'x for Arbitrary Compositions. Journal of the Korean Physical Society, 2020, 77, 1178-1182.	0.7	2
11	Dielectric Function and Critical Points of SnS0.52Se0.48 in the Temperature Range from 27 to 350 K. Journal of the Korean Physical Society, 2020, 77, 981-986.	0.7	1
12	Extended Gaussian Filtering for Noise Reduction in Spectral Analysis. Journal of the Korean Physical Society, 2020, 77, 819-823.	0.7	9
13	Anisotropic behavior of excitons in single-crystal α-SnS. AIP Advances, 2020, 10, .	1.3	9
14	Temperature dependence of the dielectric function and critical points of α-SnS from 27 to 350ÂK. Scientific Reports, 2020, 10, 18396.	3.3	11
15	Modeling of the Optical Properties of Monolayer WS2. Journal of the Korean Physical Society, 2020, 77, 298-302.	0.7	2
16	Temperature dependence of optical properties of monolayer WS2 by spectroscopic ellipsometry. Applied Surface Science, 2020, 511, 145503.	6.1	21
17	Parameterization of the Dielectric Function of GaAsSb Alloy Films. Journal of the Korean Physical Society, 2020, 77, 840-844.	0.7	1
18	Parameterization of Dielectric Functions and Phase Transitions of SrTiO3 from 26 to 674 K. Journal of Nanoscience and Nanotechnology, 2020, 20, 6692-6697.	0.9	0

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19	A Parametric Model for Temperature Dependence of Dielectric Function of AlSb Film. Journal of Nanoscience and Nanotechnology, 2019, 19, 6801-6807.	0.9	0
20	Dielectric Functions and Critical Points of GaAsSb Alloys. Journal of the Korean Physical Society, 2019, 74, 595-599.	0.7	3
21	Parameterized optical properties of monolayer MoSe2. AIP Advances, 2019, 9, .	1.3	3
22	Sub-microsecond response time deep-ultraviolet photodetectors using α-Ga2O3 thin films grown via low-temperature atomic layer deposition. Journal of Alloys and Compounds, 2019, 780, 400-407.	5.5	52
23	Temperature Dependence of the Dielectric Function of Monolayer MoSe2. Scientific Reports, 2018, 8, 3173.	3.3	13
24	Pt/Alumina Hyperbolic Metafilms with Highâ€Temperature Stability, Wide Wavelength Tunability, and Omnidirectional Absorption. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800287.	1.8	9
25	Temperature Dependence of the Dielectric Response and Critical Point Energies of Bi1.85Gd0.15Te3. Journal of Nanoscience and Nanotechnology, 2018, 18, 6321-6325.	0.9	0
26	Optical characterization of the PtSi/Si by using spectroscopic ellipsometry. Journal of the Korean Physical Society, 2016, 69, 291-296.	0.7	0
27	Temperature dependence of the critical points of monolayer MoS ₂ by ellipsometry. Applied Spectroscopy Reviews, 2016, 51, 621-635.	6.7	27
28	Parameterization of the dielectric function of InxAl1â^'xAs alloys as a function of composition. Current Applied Physics, 2015, 15, S30-S34.	2.4	5
29	Analytic representation of the dielectric function of GaN for temperatures from 26 to 690 K. Journal of the Korean Physical Society, 2014, 65, 733-738.	0.7	2
30	Ellipsometric study of the temperature dependences of the dielectric function and the critical points of AlSb at temperatures from 300 to 803 K. Journal of the Korean Physical Society, 2014, 65, 515-519.	0.7	1
31	Analytic determination of the dielectric function of InSb at energies from 0.74 to 6.42 eV at temperatures from 31 to 675 K. Journal of the Korean Physical Society, 2014, 64, 1872-1877.	0.7	1
32	Temperature dependent dielectric function and the <i>E</i> critical points of hexagonal GaN from 30 to 690 K. AIP Advances, 2014, 4, .	1.3	7
33	Reinforcement of Interfacial Adhesion of a Coated Polymer Layer on a Cobalt–Chromium Surface for Drug-Eluting Stents. Langmuir, 2014, 30, 8020-8028.	3.5	20
34	Effect of post-annealing temperature on the dielectric function of solution-processed LaAlO x /Si Films. Journal of the Korean Physical Society, 2014, 64, 1509-1513.	0.7	0
35	Parameterization of the dielectric functions of InGaSb alloys. Current Applied Physics, 2014, 14, 768-771.	2.4	2
36	Influences of rapid thermal process on solution-deposited Ti-silicate/Si films: Phase segregation, composition and interface changes, and dielectric properties. Materials Chemistry and Physics, 2014, 145, 168-175.	4.0	6

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37	Interband transitions and dielectric functions of InGaSb alloys. Applied Physics Letters, 2013, 102, .	3.3	6
38	Application of rapid thermal process to solution-processed Ti-silicate films for enhancing permittivity without losing amorphous nature. Current Applied Physics, 2013, 13, S41-S44.	2.4	2
39	Optical properties of AlAsxSb1â^'x alloys determined by in situ ellipsometry. Applied Physics Letters, 2013, 103, 011901.	3.3	4
40	Optical properties of solution-processed LaAlOx/Si films using spectroscopic ellipsometry. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 04D110.	1.2	3
41	Temperature dependence of the dielectric functions and the critical points of InSb by spectroscopic ellipsometry from 31 to 675 K. Journal of Applied Physics, 2013, 114, .	2.5	15
42	Temperature-dependent optical properties of epitaxial CdO thin films determined by spectroscopic ellipsometry and Raman scattering. Journal of Applied Physics, 2013, 113, 183515.	2.5	11
43	Stability of UV exposed RR-P3BT films by spectroscopic ellipsometry. , 2013, , .		0
44	Parameterization of the dielectric function of InP from 1.19 to 6.57 eV for temperatures from 25 to 700 K. Journal of Applied Physics, 2012, 112, .	2.5	6
45	Investigation of the Dielectric Function of Solution-Processed InGaZnO Films Using Ellipsometry. Journal of Nanoscience and Nanotechnology, 2012, 12, 5804-5807.	0.9	1
46	Parametric modeling of the dielectric function and identification of the critical point of a CdMgTe alloy in the vacuum ultraviolet spectral range. Journal of the Korean Physical Society, 2012, 60, 1219-1223.	0.7	0
47	Parametric model dielectric functions of InAs for temperatures from 22 to 675 K. Journal of the Korean Physical Society, 2012, 61, 1821-1825.	0.7	4
48	Investigation of InSb critical-point energies at 25 K by using spectroscopic ellipsometry. Journal of the Korean Physical Society, 2012, 61, 439-443.	0.7	1
49	Dielectric function and energy of the E 0 critical point of hexagonal GaN at 26 K studied by using spectroscopic ellipsometry. Journal of the Korean Physical Society, 2012, 61, 791-794.	0.7	2
50	Temperature dependence of the dielectric function and critical-point energies of InAs. Journal of the Korean Physical Society, 2012, 61, 97-101.	0.7	6
51	Investigation of the Crystallization of Amorphous Si by Imaging Ellipsometry. Journal of Nanoscience and Nanotechnology, 2011, 11, 6198-6202.	0.9	Ο
52	Temperature dependence of the dielectric response of AlSb. , 2011, , .		1
53	Optical study of sol-gel processed ZrO2/Si films by spectroscopic ellipsometry. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 04D108.	1.2	7
54	Effect of the Ga Ratio on the Dielectric Function of Solution-processed InGaZnO Films. Journal of the Korean Physical Society, 2011, 59, 3396-3400.	0.7	4

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55	In-situ study of molecular dynamics in a water environment by using imaging ellipsometry. Advances in Natural Sciences: Nanoscience and Nanotechnology, 2010, 1, 045003.	1.5	0
56	Dielectric functions and interband transitions of In1â^'xAlxSb alloys. Applied Physics Letters, 2010, 97, .	3.3	6
57	InAs critical-point energies at 22 K from spectroscopic ellipsometry. Applied Physics Letters, 2010, 97, 171912.	3.3	21
58	Interband transitions of InAsxSb1â^'x alloy films. Applied Physics Letters, 2009, 95, 111902.	3.3	24
59	Imaging of Collapsed Fatty Acid Films at Airâ^'Water Interfaces. Langmuir, 2009, 25, 9262-9269.	3.5	22
60	Characterization of Si nanorods by spectroscopic ellipsometry with efficient theoretical modeling. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 876-879.	1.8	31
61	Overlayer effects in the critical-point analysis of ellipsometric spectra: Application to InxGa1â^'xAs alloys. Journal of Applied Physics, 2008, 103, .	2.5	4
62	Model dielectric functions for AlxGa1â^'xAs alloys of arbitrary compositions. Journal of Applied Physics, 2008, 104, 013515.	2.5	13
63	Direct Imaging of a Collapsed Langmuir Monolayer and Multilayer Formation. Journal of the Korean Physical Society, 2008, 53, 1488-1491.	0.7	1
64	Optical Properties of GaN by Using Ellipsometry and a Band Calculation. Journal of the Korean Physical Society, 2008, 53, 1575-1579.	0.7	10
65	Dielectric Functions of CdSe and ZnSe Obtained by Using Vacuum Ultra-Violet Spectroscopic Ellipsometry. Journal of the Korean Physical Society, 2007, 50, 806.	0.7	6
66	Dielectric functions ofInxGa1â^'xAsalloys. Physical Review B, 2003, 68, .	3.2	43